Silicon PNP Power Transistors 2N6469

DESCRIPTION

·With TO-3 package
·Low collector saturation voltage
·Excellent safe operating area
·High gain at high current

APPLICATIONS

·General-purpose of switching and linear-amplifier applications

PINNING

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector



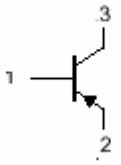


Fig.1 simplified outline (TO-3) and symbol

Absolute maximum ratings(Ta=□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-50	V
V_{CEO}	Collector-emitter voltage	Open base	-40	V
V_{EBO}	Emitter-base voltage	Open collector	-5	V
I_C	Collector current		-15	A
I_B	Base current		-5	A
P_T	Total power dissipation	T_C=25□	125	W
T_j	Junction temperature		200	□
T_{stg}	Storage temperature		-65~200	□

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
$R_{th\ j\text{-}c}$	Thermal resistance junction to case	1.4	□/W

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CHARACTERISTICS

Tj=25□ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-emitter sustaining voltage	I_C=-0.2A ;I_B=0	-40			V
$V_{CEsat-1}$	Collector-emitter saturation voltage	I_C=-5A; I_B=-0.5A			-1.3	V
$V_{CEsat-2}$	Collector-emitter saturation voltage	I_C=-15A; I_B=-3A			-3.5	V
V_{BE}	Base-emitter on voltage	I_C=-15A ; V_{CE}=-4V			-3.5	V
I_{CEO}	Collector cut-off current	V_{CE}=-20V; I_B=0			1.0	mA
I_{CEX}	Collector cut-off current	V_{CE}=-45V; V_{BE}=-1.5V T_C=150□			-0.2 -5.0	mA
I_{EBO}	Emitter cut-off current	V_{EB}=-5V; I_C=0			-5	mA
h_{FE-1}	DC current gain	I_C=-5A ; V_{CE}=-4V	20		150	
h_{FE-2}	DC current gain	I_C=-15A ; V_{CE}=-4V	5			
f_T	Transition frequency	I_C=-0.5A ; V_{CE}=-10V	4			MHz

PACKAGE OUTLINE

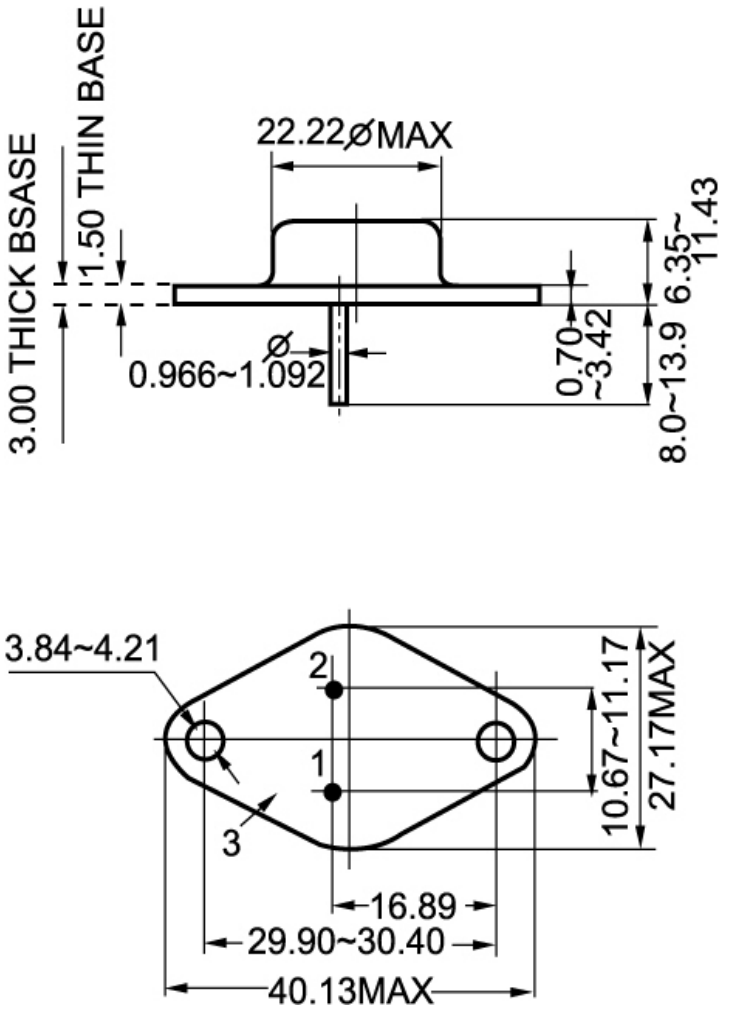


Fig.2 outline dimensions (unindicated tolerance:±0.1mm)